

CLAIMS

What is claimed is:

- 1 1. A spin valve magnetoresistance sensor, comprising:
2 a base layer layered on top of a substrate, the base layer including
3 a first base film having a nonmagnetic metal and a second base film
4 formed on top of the first base film, the second base film having an alloy
5 represented by NiFeX, wherein X includes one of Cr, Nb and Rh, the
6 second base film having a face-centered cubic (fcc) structure and a (111)
7 orientation;
8 a pair of magnetic layers enclosing a nonmagnetic layer layered on
9 top of the base layer; and
10 an antiferromagnetic layer adjacent to one of the pair of magnetic
11 layers.
- 1 2. The spin valve magnetoresistance sensor described in claim
2 1 wherein a film thickness of the second base film is within a range of 20
3 to 100Å.
- 1 3. The spin valve magnetoresistance sensor of claim 1 wherein
2 X is Cr, wherein a content of Cr in the second base film is within a range
3 of 20 to 50 at%.

- 1 4. The spin valve magnetoresistance sensor of claim 1 wherein
- 2 the spin valve magnetoresistance sensor is included in a thin film
- 3 magnetic head.